#### **EECE 481**

#### Noise Margin In Digital Circuits Lecture 4

#### Reza Molavi Dept. of ECE University of British Columbia reza@ece.ubc.ca

Slides Courtesy : Dr. Res Saleh (UBC), Dr. D. Sengupta (AMD), Dr. B. Razavi (UCLA)

#### Overview

- Background
  - Digital IC designs must operate properly in noisy environments. We would like to have some notion of how robust a circuit is to external noise sources. There are a variety of measures of noise for logic circuits such as single stage noise margin (SSNM) and the classical noise margins are based on the unity gain points of the VTC. These metrics eventually lead us to desirable properties that logic gates must have in order to work properly. We will look at how to calculate this for inverters in the next lecture.

## Noise Margin and Sensitivity

- Robustness of a circuit (i.e., its ability to operate properly in the presence of noise) depends on two factors:
  - 1. Noise margins (voltage metric)
    - how much noise can we apply before the gate fails
    - many different ways to measure this
  - 2. Noise sensitivity
    - how much noise can actually couple into the gate
    - depends on gate type and its connection to noise source
- First component sets requirements on the gate to handle noise
- Second component captures the response of the circuit to a given noise input (will be discussed in later)
- Start by examining the first issue using basic inverter circuit...

## Ideal Inverter Characteristics (VTC)



## Physical Inverter Characteristics (VTC)



## Noise Attenuation

- What does this type of VTC imply about a noisy signal as it passes through a logic gate?
- Noise is reduced:  $V_{II} \rightarrow V_{IN} \rightarrow V_{alid \ Logic \ 1} \rightarrow V_{OUT} \rightarrow V_{OUH}$  $V_{II} \rightarrow V_{alid \ Logic \ 0} \rightarrow V_{OUT} \rightarrow V_{OUH}$
- Next, consider metrics for noise tolerance and the implications on the characteristics of the gate

## The Regenerative Property

• A gate with regenerative property ensure that a disturbed signal converges back to a nominal voltage level  $v_0$   $v_1$   $v_2$   $v_3$   $v_4$   $v_5$   $v_6$ 



# Single Source Noise Margin (SSNM)

- Simplest type of noise margin is the single-stage noise margin
- Defined as maximum noise, v<sub>n</sub>, in a single stage that still allows subsequent stages to recover to the right value (regenerative property)



- In the above circuit  $V_{i2} = V_{o1} v_n = V_{OH} v_n$
- For noise added to a high level input, the correct levels will be maintained if  $V_{\rm OH}$   $v_{\rm n}$  >  $V_{\rm TH}$
- For noise added to a low level input, correct levels will be maintained if  $V_{OL}$  +  $v_n$  <  $V_{TH}$

#### Single Source Noise Margin – Cont'd



#### Single Source Noise Margin – Cont'd



## Multi Stage Noise Margin (MSNM)

 Noise actually occurs between every gate and not at a single stage, as we have assumed so far



- In the above circuit, we need to determine how much noise we can tolerate before the circuit stops working as expected
- We note that Vout = f(Vin)
- With noise Vout' = f(Vin) + Vnoise x Gain + Higher-order terms
- If the Gain < 1, then noise is attenuated; otherwise it is amplified
- IDEA: Develop a metric based on keeping the Gain < 1</li>

#### **Classical Noise Margin**



## Requirements for a Valid Logic Gate

- Must have a high gain region between two low gain regions
- Gain must be below 1 for low gain regions
- Gain must be greater than 1 for high gain region
- Output must swing from valid low to valid high
  - Low output should be below  $V_{IL}$
  - High output should be above  $V_{\rm IH}$



- Noise margin expresses the ability of a circuit to overpower a noise source
  - noise sources: supply noise, cross talk, interference, offset
- Noise immunity expresses the ability of the system to process and transmit information correctly in the presence of noise
- For good noise immunity, the signal swing (i.e., the difference between  $V_{OH}$  and  $V_{OL}$ ) and the noise margin have to be large enough to overpower the impact of fixed sources of noise

 Basic structure of MOS inverter is shown below: NMOS pulldown device with a variety of possible pullup devices



We will derive the noise margin parameters for different types of inverters